

### General Description

The WSD20L120DN56 is the highest performance trench P-Ch MOSFET with extreme high cell density, which provide excellent R<sub>DS(on)</sub> and gate charge for most of the synchronous buck converter applications.

The WSD20L120DN56 meet the RoHS and Green Product requirement 100% EAS guaranteed with full function reliability approved.

### Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

### Absolute Maximum Ratings

Symbol	Parameter	Rating		Units
		10s	Steady State	
V <sub>DS</sub>	Drain-Source Voltage	-20		V
V <sub>GS</sub>	Gate-Source Voltage	±10		V
I <sub>D</sub> @T <sub>C</sub> =25°C	Continuous Drain Current, V <sub>GS</sub> @ -10V <sup>1</sup>	-120		A
I <sub>D</sub> @T <sub>C</sub> =100°C	Continuous Drain Current, V <sub>GS</sub> @ -10V <sup>1</sup>	-69.5		A
I <sub>D</sub> @T <sub>A</sub> =25°C	Continuous Drain Current, V <sub>GS</sub> @ -10V <sup>1</sup>	-25	-22	A
I <sub>D</sub> @T <sub>A</sub> =70°C	Continuous Drain Current, V <sub>GS</sub> @ -10V <sup>1</sup>	-24	-18	A
I <sub>DM</sub>	Pulsed Drain Current <sup>2</sup>	-340		A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	300		mJ
I <sub>AS</sub>	Avalanche Current	-36		A
P <sub>D</sub> @T <sub>C</sub> =25°C	Total Power Dissipation <sup>4</sup>	130		W
P <sub>D</sub> @T <sub>A</sub> =25°C	Total Power Dissipation <sup>4</sup>	6.8	6.25	W
T <sub>STG</sub>	Storage Temperature Range	-55 to 150		°C
T <sub>J</sub>	Operating Junction Temperature Range	-55 to 150		°C

### Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R <sub>θJA</sub>	Thermal Resistance Junction-Ambient <sup>1</sup>	---	54	°C/W
R <sub>θJA</sub>	Thermal Resistance Junction-Ambient <sup>1</sup> (t ≤ 10s)	---	18	°C/W
R <sub>θJC</sub>	Thermal Resistance Junction-Case <sup>1</sup>	---	1.6	°C/W

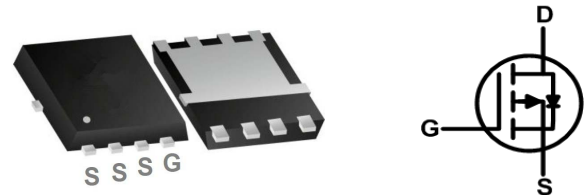
### Product Summary

BVDSS	R <sub>DS(on)</sub>	I <sub>D</sub>
-20V	2.1mΩ	-120A

### Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

### DFN5X6-8 Pin Configuration



**Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	-20	---	---	V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	BVDSS Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =-1mA	---	-0.0212	---	V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-20A	---	2.1	2.7	mΩ
		V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-20A	---	2.8	3.7	
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =-250uA	-0.4	-0.6	-1.0	V
ΔV <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient		---	4.8	---	mV/°C
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =-20V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	-1	uA
		V <sub>DS</sub> =-20V, V <sub>GS</sub> =0V, T <sub>J</sub> =55°C	---	---	-6	
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =-5V, I <sub>D</sub> =-20A	---	100	---	S
R <sub>g</sub>	Gate Resistance	V <sub>DS</sub> =0V, V <sub>GS</sub> =0V, f=1MHz	---	2	5	Ω
Q <sub>g</sub>	Total Gate Charge (-4.5V)	V <sub>DS</sub> =-10V, V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-20A	---	100	---	nC
Q <sub>gs</sub>	Gate-Source Charge		---	21	---	
Q <sub>gd</sub>	Gate-Drain Charge		---	32	---	
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> =-10V, V <sub>GEN</sub> =-4.5V, R <sub>G</sub> =3Ω, I <sub>D</sub> =-1A, R <sub>L</sub> =0.5Ω	---	20	---	ns
T <sub>r</sub>	Rise Time		---	50	---	
T <sub>d(off)</sub>	Turn-Off Delay Time		---	100	---	
T <sub>f</sub>	Fall Time		---	40	---	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =-10V, V <sub>GS</sub> =0V, f=1MHz	---	4950	---	pF
C <sub>oss</sub>	Output Capacitance		---	380	---	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	290	---	

**Guaranteed Avalanche Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
EAS	Single Pulse Avalanche Energy <sup>5</sup>	V <sub>DD</sub> =-25V, L=0.5mH, I <sub>AS</sub> =-36A	300	---	---	mJ

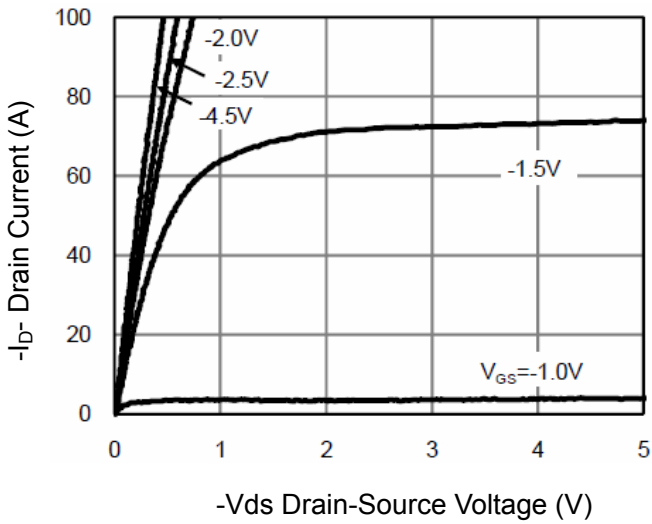
**Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current <sup>1,6</sup>	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	-70	A
I <sub>SM</sub>	Pulsed Source Current <sup>2,6</sup>		---	---	-280	A
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V, I <sub>S</sub> =-1A, T <sub>J</sub> =25°C	---	---	-1.2	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> =-15A, dI/dt=100A/μs,	---	48	---	nS
Q <sub>rr</sub>	Reverse Recovery Charge	T <sub>J</sub> =25°C	---	55	---	nC

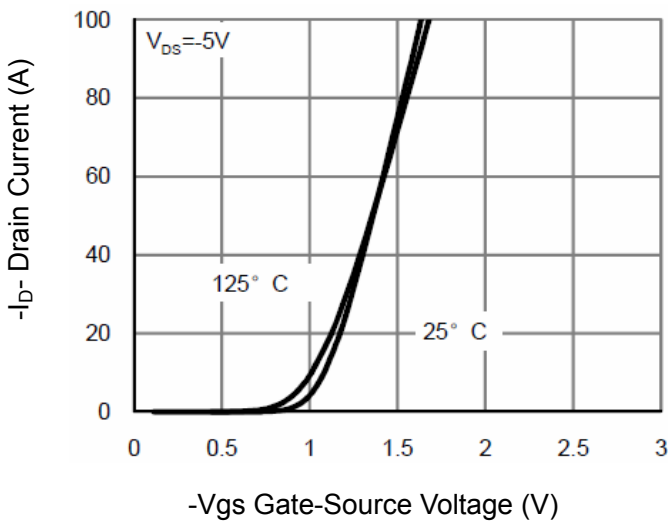
Note :

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 20Z copper, t<10sec.
- 2.The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- 3.The EAS data shows Max. rating. The test condition is V<sub>DD</sub>=-25V, V<sub>GS</sub>=-10V, L=0.5mH, I<sub>AS</sub>=-36A
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The Min. value is 100% EAS tested guarantee.
- 6.The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub>, in real applications, should be limited by total power dissipation.

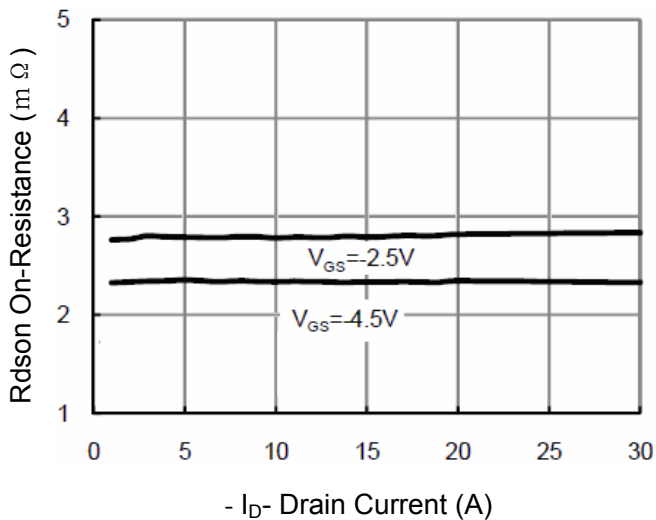
**Typical Characteristics**



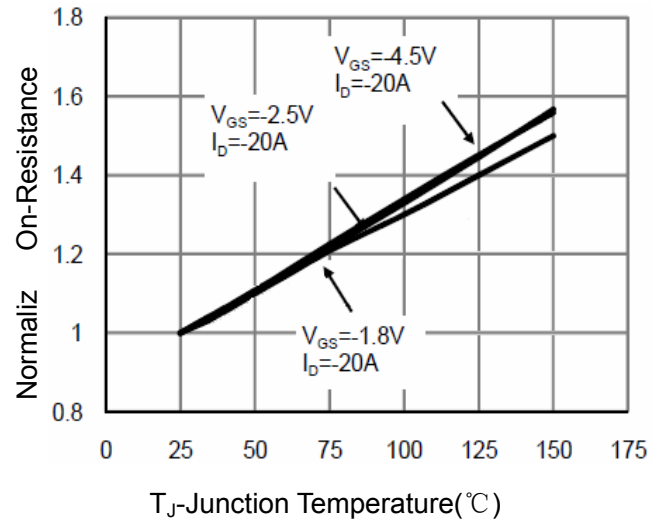
**Figure 1 Output Characteristics**



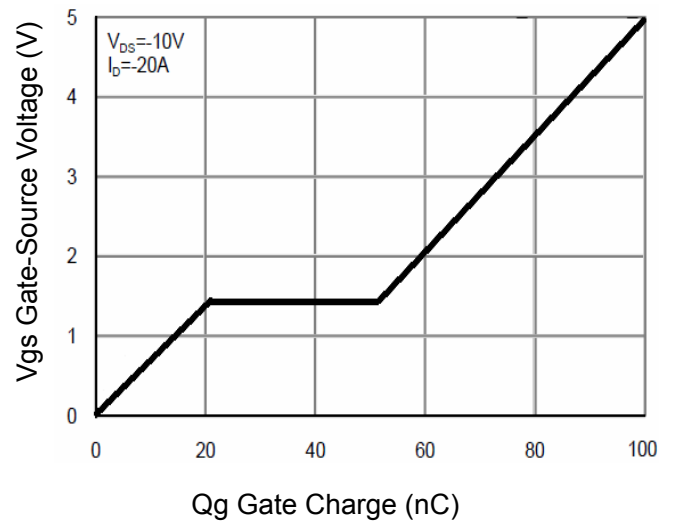
**Figure 2 Transfer Characteristics**



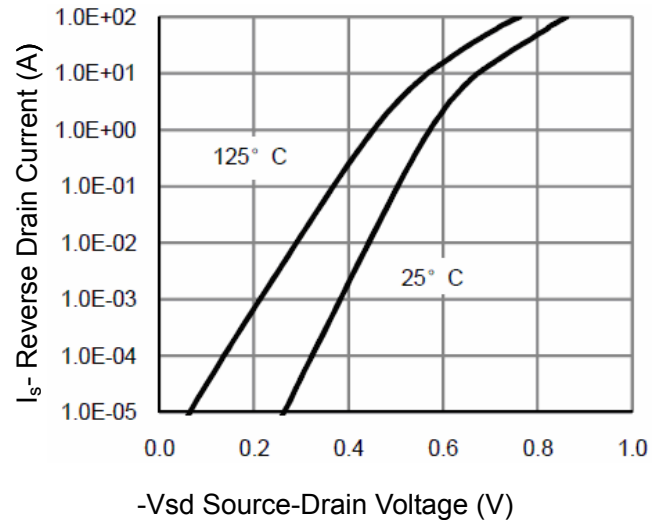
**Figure 3 Rdson- Drain Current**



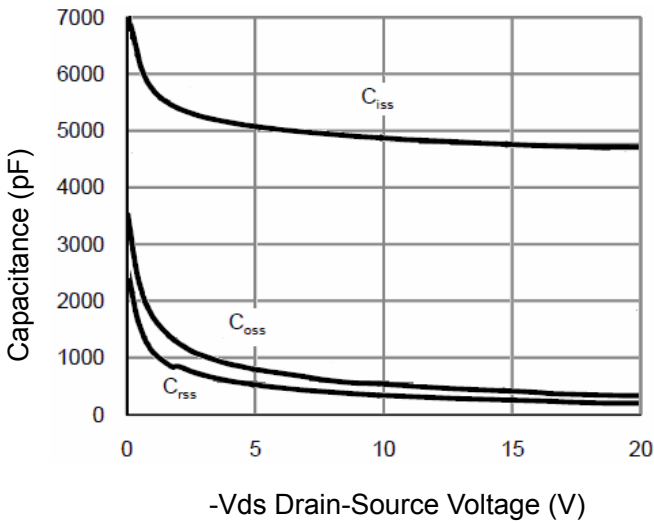
**Figure 4 Rdson-Junction Temperature**



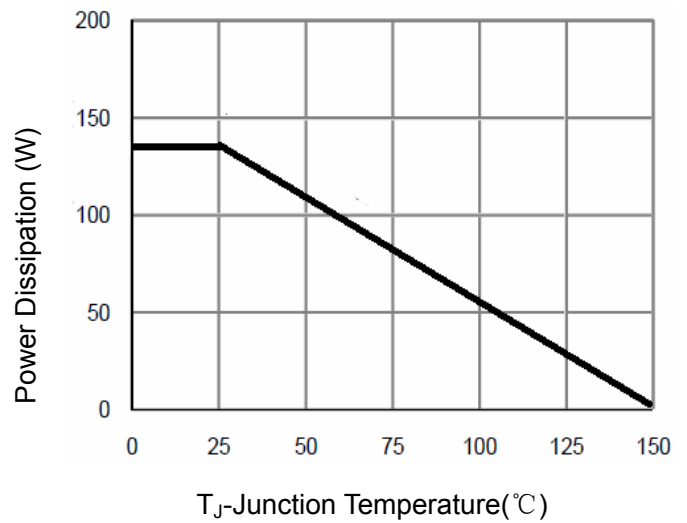
**Figure 5 Gate Charge**



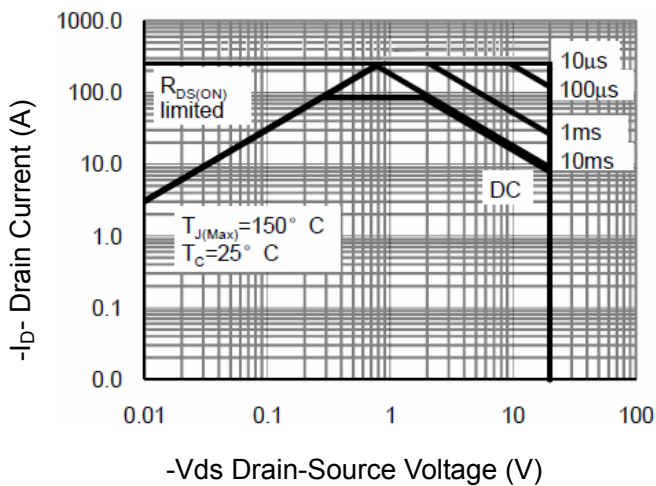
**Figure 6 Source- Drain Diode Forward**



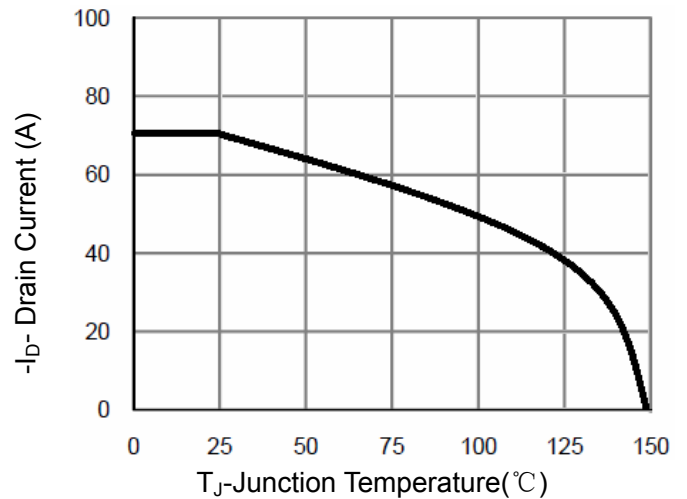
**Figure 7 Capacitance vs Vds**



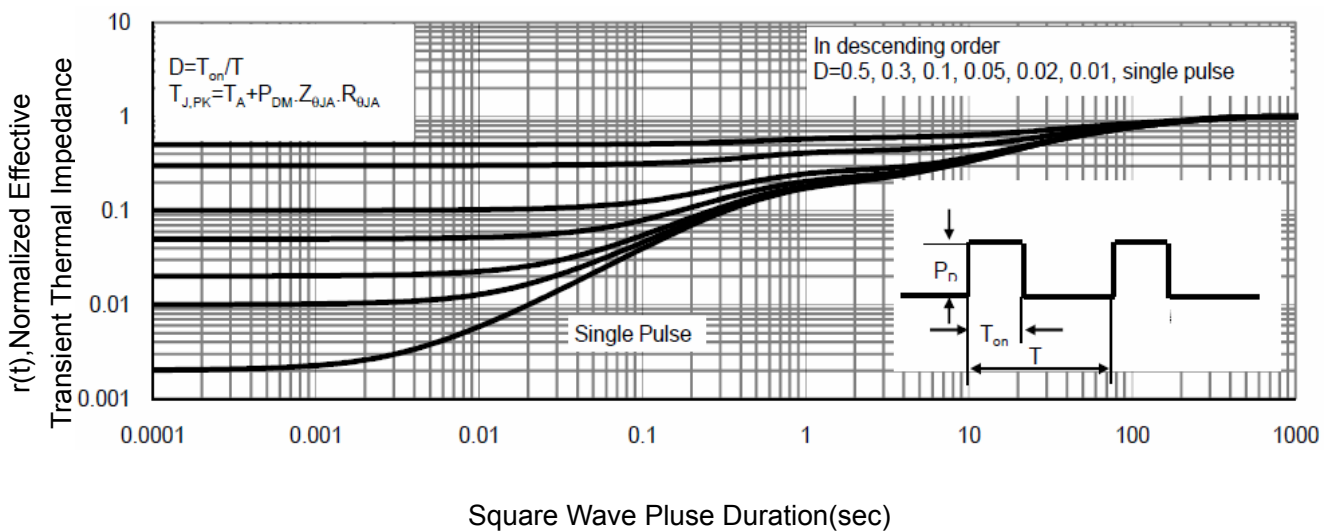
**Figure 9 Power De-rating**



**Figure 8 Safe Operation Area**



**Figure 10 -Current De-rating**



**Figure 11 Normalized Maximum Transient Thermal Impedance**

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